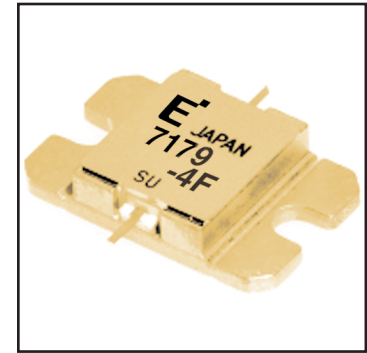


### FEATURES

- High Output Power:  $P_{1dB} = 36.5\text{dBm}$  (Typ.)
- High Gain:  $G_{1dB} = 9.0\text{dB}$  (Typ.)
- High PAE:  $\eta_{add} = 35\%$  (Typ.)
- Low  $IM_3 = -46\text{dBc}$  @  $P_o = 25.5\text{dBm}$
- Broad Band: 7.1 ~ 7.9GHz
- Impedance Matched  $Z_{in}/Z_{out} = 50\Omega$
- Hermetically Sealed Package

### DESCRIPTION

The FLM7179-4F is a power GaAs FET that is internally matched for standard communication bands to provide optimum power and gain in a 50 ohm system.



Eudyna's stringent Quality Assurance Program assures the highest reliability and consistent performance.

### ABSOLUTE MAXIMUM RATING (Ambient Temperature $T_a=25^\circ\text{C}$ )

Item	Symbol	Condition	Rating	Unit
Drain-Source Voltage	$V_{DS}$		15	V
Gate-Source Voltage	$V_{GS}$		-5	V
Total Power Dissipation	$P_T$	$T_c = 25^\circ\text{C}$	25.0	W
Storage Temperature	$T_{stg}$		-65 to +175	$^\circ\text{C}$
Channel Temperature	$T_{ch}$		175	$^\circ\text{C}$

Fujitsu recommends the following conditions for the reliable operation of GaAs FETs:

1. The drain-source operating voltage ( $V_{DS}$ ) should not exceed 10 volts.
2. The forward and reverse gate currents should not exceed 16.0 and -2.2 mA respectively with gate resistance of 100 $\Omega$ .

### ELECTRICAL CHARACTERISTICS (Ambient Temperature $T_a=25^\circ\text{C}$ )

Item	Symbol	Test Conditions	Limit			Unit
			Min.	Typ.	Max.	
Saturated Drain Current	$I_{DSS}$	$V_{DS} = 5\text{V}, V_{GS} = 0\text{V}$	-	1700	2600	mA
Transconductance	$g_m$	$V_{DS} = 5\text{V}, I_{DS} = 1100\text{mA}$	-	1700	-	mS
Pinch-off Voltage	$V_p$	$V_{DS} = 5\text{V}, I_{DS} = 85\text{mA}$	-0.5	-1.5	-3.0	V
Gate Source Breakdown Voltage	$V_{GSO}$	$I_{GS} = -85\mu\text{A}$	-5.0	-	-	V
Output Power at 1dB G.C.P.	$P_{1dB}$	$V_{DS} = 10\text{V},$ $I_{DS} = 0.65 I_{DSS}$ (Typ.), $f = 7.1 \sim 7.9\text{GHz},$ $Z_S = Z_L = 50\text{ohm}$	35.5	36.5	-	dBm
Power Gain at 1dB G.C.P.	$G_{1dB}$		8.0	9.0	-	dB
Drain Current	$I_{dsr}$		-	1100	1300	mA
Power-added Efficiency	$\eta_{add}$		-	35	-	%
Gain Flatness	$\Delta G$		-	-	$\pm 0.6$	dB
3rd Order Intermodulation Distortion	$IM_3$	$f = 7.9\text{GHz}, \Delta f = 10\text{MHz}$ 2-Tone Test $P_{out} = 25.5\text{dBm S.C.L.}$	-44	-46	-	dBc
Thermal Resistance	$R_{th}$	Channel to Case	-	5.0	6.0	$^\circ\text{C/W}$
Channel Temperature Rise	$\Delta T_{ch}$	$10\text{V} \times I_{dsr} \times R_{th}$	-	-	80	$^\circ\text{C}$

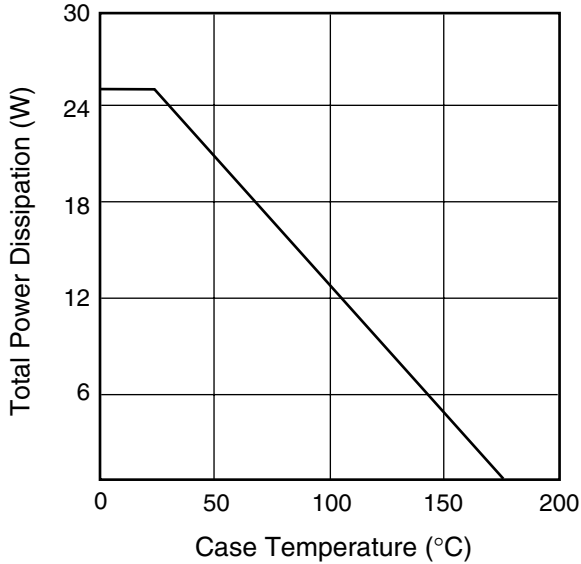
CASE STYLE: IB

G.C.P.: Gain Compression Point, S.C.L.: Single Carrier Level

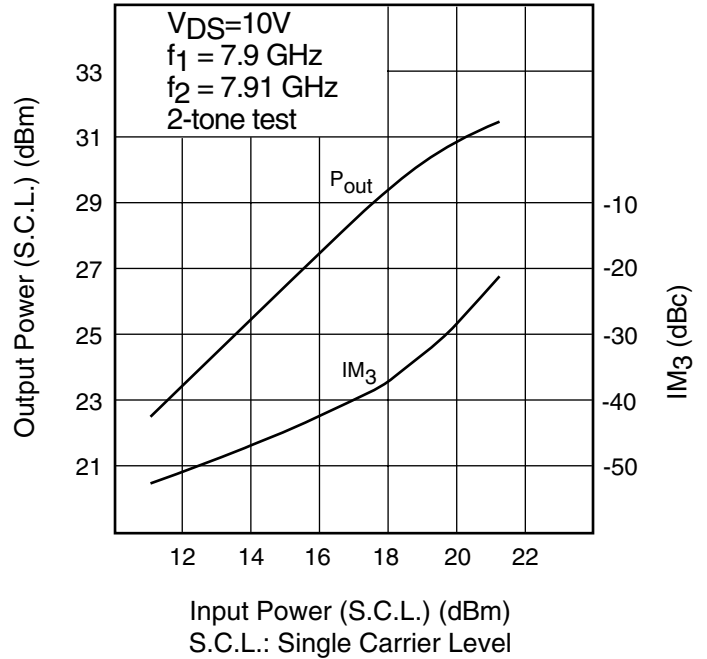
# FLM7179-4F

## C-Band Internally Matched FET

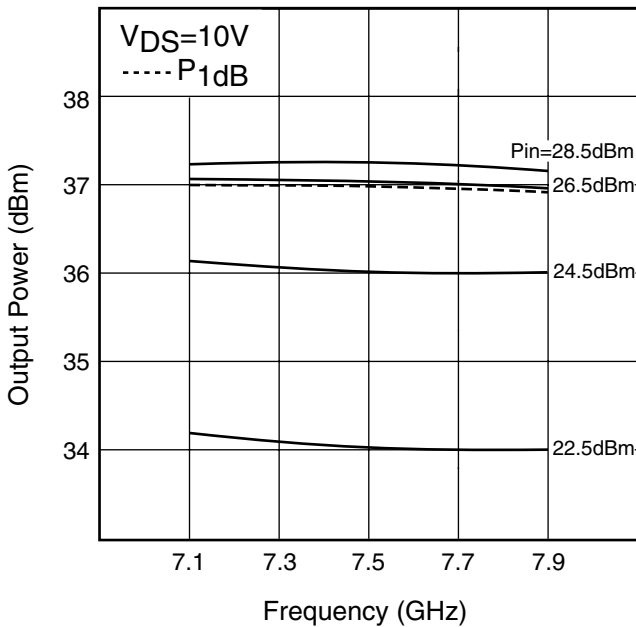
**POWER DERATING CURVE**



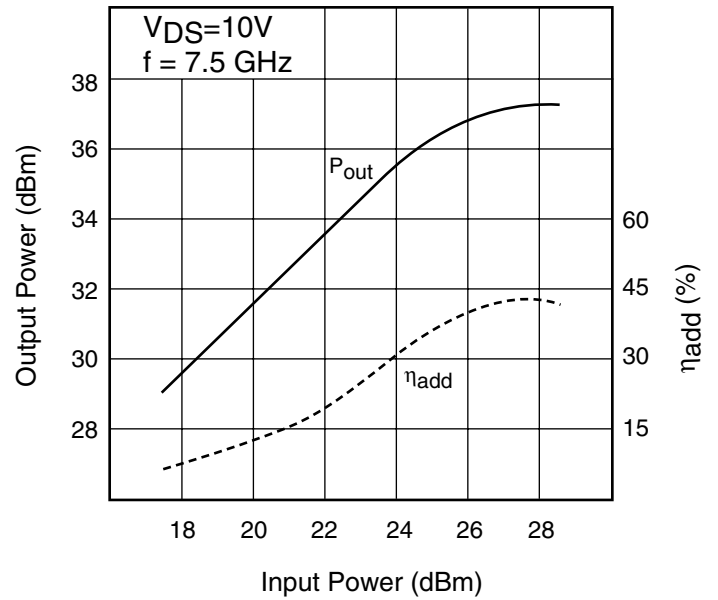
**OUTPUT POWER & IM<sub>3</sub> vs. INPUT POWER**

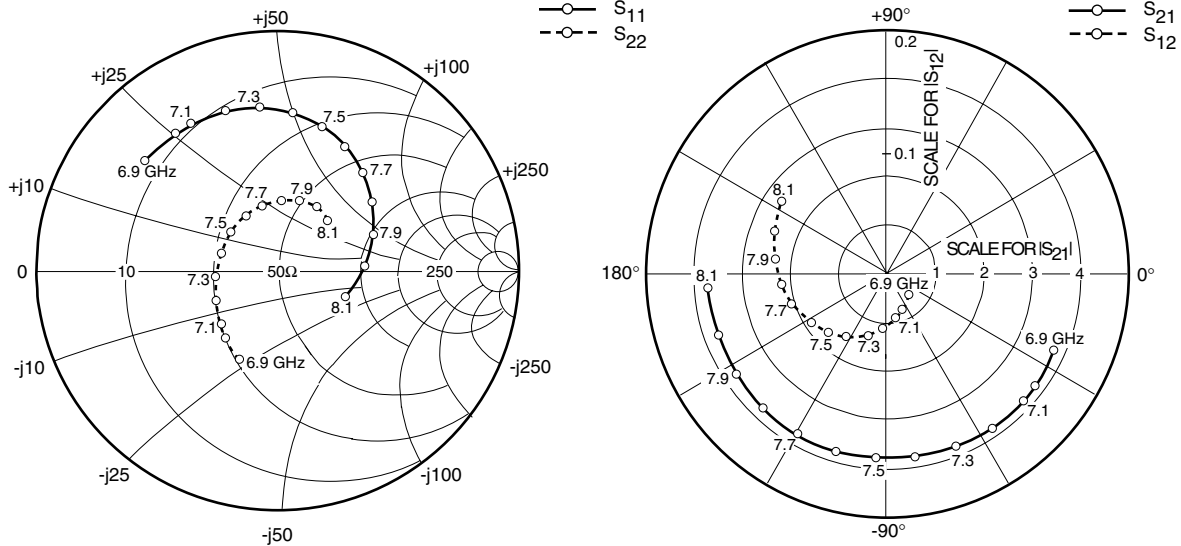


**OUTPUT POWER vs. FREQUENCY**



**OUTPUT POWER vs. INPUT POWER**





### S-PARAMETERS

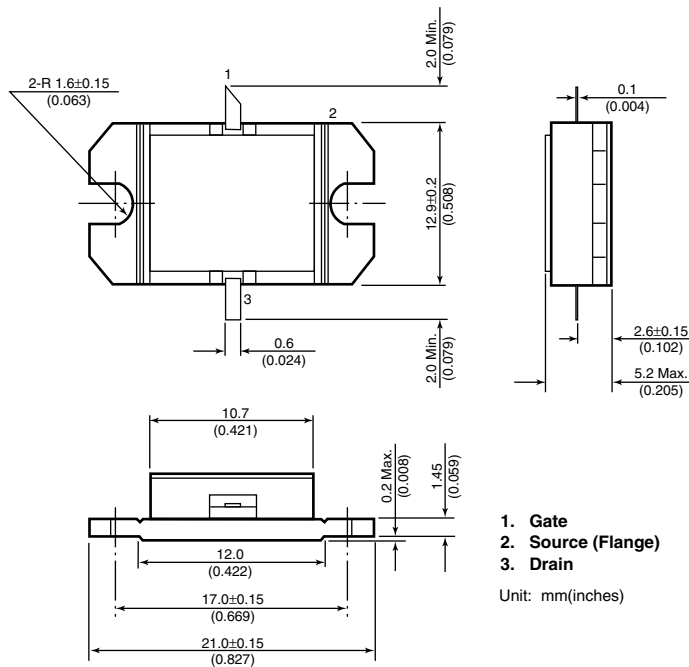
$V_{DS} = 10V, I_{DS} = 1100mA$

FREQUENCY (MHZ)	S11		S21		S12		S22	
	MAG	ANG	MAG	ANG	MAG	ANG	MAG	ANG
6900	.712	140.3	3.823	-24.3	.025	-45.8	.402	-113.7
7000	.714	127.0	3.840	-37.1	.032	-67.6	.354	-127.8
7100	.710	120.5	3.850	-42.7	.036	-77.9	.324	-136.3
7200	.701	108.1	3.852	-55.5	.045	-93.2	.288	-154.2
7300	.684	96.2	3.831	-68.0	.053	-106.9	.259	-175.1
7400	.658	84.6	3.820	-80.9	.061	-122.3	.249	162.0
7500	.625	73.0	3.804	-93.5	.068	-135.6	.251	140.4
7600	.584	61.4	3.783	-106.3	.075	-148.9	.262	120.3
7700	.535	49.2	3.768	-119.4	.082	-162.2	.275	102.2
7800	.481	36.1	3.756	-132.6	.088	-174.2	.295	86.7
7900	.421	20.8	3.744	-146.1	.093	172.4	.307	72.3
8000	.359	2.3	3.726	-160.0	.100	159.7	.305	59.4
8100	.300	-22.5	3.708	-174.9	.106	145.5	.293	45.9

# FLM7179-4F

## C-Band Internally Matched FET

### Case Style "IB" Metal-Ceramic Hermetic Package



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#### CAUTION

Eudyna Devices Inc. products contain **gallium arsenide (GaAs)** which can be hazardous to the human body and the environment. For safety, observe the following procedures:

- Do not put this product into the mouth.
- Do not alter the form of this product into a gas, powder, or liquid through burning, crushing, or chemical processing as these by-products are dangerous to the human body if inhaled, ingested, or swallowed.
- Observe government laws and company regulations when discarding this product. This product must be discarded in accordance with methods specified by applicable hazardous waste procedures.

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